

UNISONIC TECHNOLOGIES CO., LTD

UT2804 Preliminary Power MOSFET

N-CHANNEL LOGIC LEVEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

■ DESCRIPTION

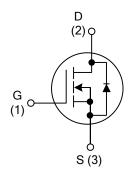
The UTC **UT2804** uses advanced technology to provide fast switching speed, ruggedized device design, low on-resistance and cost-effectiveness.

The UTC **UT2804** is suitable for low-profile applications with through-hole version and low voltage applications such as DC/DC converters.

■ FEATURES

- * Low On-Resistance
- * Simple Drive Requirement
- * Fast Switching Speed

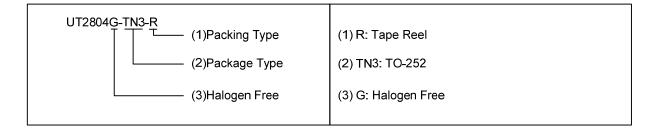
■ SYMBOL

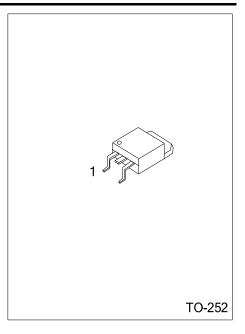


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing	
Lead Free	Halogen Free	TO 252	1	2	3	Facking	
UT2804G-TN3-R	UT2804L-TN3-R	TO-252	G	D	S	Tape Reel	

Note: G: Gate, D: Drain, S: Source





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■ **ABSOLUTE MAXIMUM RATINGS** (TC = 25°C Unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DS}	40	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current	T _C =25°C	l _D	10	Α	
	T _C =100°C		8	^	
Pulsed Drain Current (Note 2)		I _{DM}	40	Α	
Power Dissipation	T _C =25°C	P _D	32	W	
1 Ower Dissipation	T _C =100°C	ID	22	V V	
Operating Junction Temperature		TJ	-55 ~ 150	°C	
Storage Temperature		T _{STG}	-55 ~ 150	°C	

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Pulse width limited by maximum junction temperature.
- 3. Duty cycle ≤ 1%

■ THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$ heta_{JA}$	75	°C/W
Junction to Case	θ_{JC}	3	°C/W

■ **ELECTRICAL CHARACTERISTICS** (TC =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	I _D =250μA, V _{GS} =0V				V
Drain-Source Leakage Current	I _{DSS}	V_{DS} =32V, V_{GS} =0V			1	μA
		V _{DS} =30V, V _{GS} =0V, T _C =125°C			10	μΑ
Gate-Source Leakage Current	I_{GSS}	V _{DS} =0V, V _{GS} =±20V			±250	nA
On-State Drain Current (Note 1)	$I_{D(ON)}$	V _{DS} =10V, V _{GS} =10V	40			Α
ON CHARACTERISTICS				-	-	-
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1	1.5	2.5	V
Static Drain-Source On-State	В	V_{GS} =-4.5V, I_D =8A		30	42	mΩ
Resistance (Note 1)	$R_{DS(ON)}$	V _{GS} =10V, I _D =10A		21	28	11122
Forward Transconductance (Note 1)	g fs	V _{DS} =10V, I _D =10A		19		S
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V _{GS} =0V, V _{DS} =10V, f=1MHz		790		pF
Output Capacitance	Coss			175		pF
Reverse Transfer Capacitance	C_{RSS}			65		pF
SWITCHING PARAMETERS (Note 2)			_	_	_	
Total Gate Charge	Q_{G}	V _{GS} =10V, V _{DS} =0.5V _{(BR)DSS} , I _D =10A		16		nC
Gate to Source Charge	Q_GS			2.5		nC
Gate to Drain Charge	Q_GD			2.1		nC
Turn-ON Delay Time	$t_{D(ON)}$	V_{GS} =10V, V_{DS} =20V, I_{D} \tilde{1} 1A, R_{GS} =6\Omega, R_{L} =1\Omega		2.2	4.4	ns
Rise Time	t_R			7.5	15	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			11.8	21.3	ns
Fall-Time	t_{F}			3.7	7.4	ns
SOURCE- DRAIN DIODE RATINGS A	ND CHARACT	TERISTICS				
Drain-Source Diode Forward Voltage		I _F =I _S , V _{GS} =0V			1	V
(Note 1)	V _{SD}				ı	V
Reverse Recovery Time	t _{RR}	-I _F =5A, dI _F /dt=100A/μs		15.5		ns
Reverse Recovery Charge	Q_{RR}			7.9		nC
Continuous Current	Is				1.3	Α
Pulsed Current (Note 3)	I_{SM}				2.6	Α

Note: 1. Pulse test: Pulse Width ≤ 300µsec, Duty Cycle ≤ 2%.

- 2. Independent of operating temperature.
- 3. Pulse width limited by maximum junction temperature.



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